

INFORMATION DISCLOSURE
CITATION IN AN
APPLICATION

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APPLICANT
Hidenori KAMEI, et al.

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GROUP

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U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
<i>Dme</i>	5,932,896	8/3/99	Sugiura et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>Dme</i>	"p-type Conduction in As-Grown Mg-Doped GaN Grown by Metalorganic Chemical Vapor Deposition" by Sugiura et al., Applied Physics Letters, Vol. 72, No. 14 (April 6, 1998), pp. 1748-1750.

EXAMINER <i>D.M. Collins</i>	DATE CONSIDERED <i>1-2-02</i>
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